



# **On-chip evaluation of voltage fluctuations and fault occurrence induced by Si backside EM injection**

April 9<sup>th</sup>, 2024

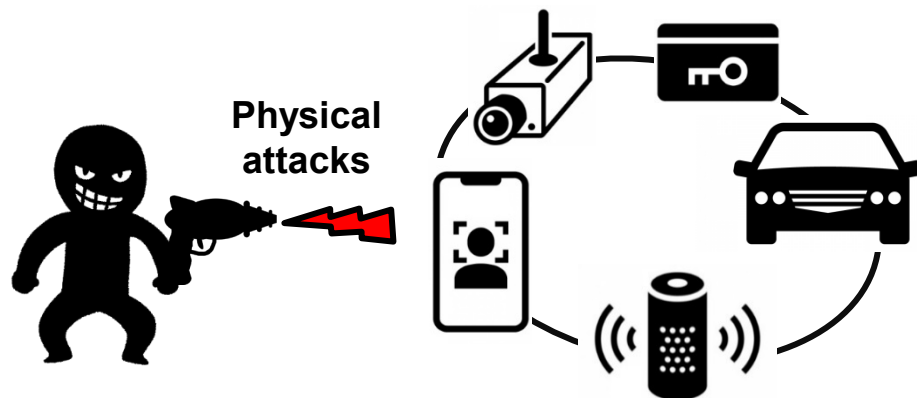
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# Threats of fault injection

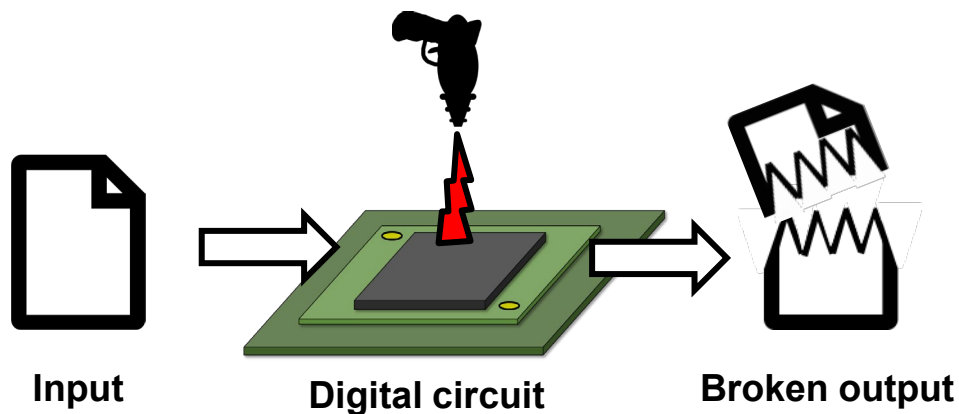
## ▶ Security of semiconductor devices

- ✓ Physical attack threats



## ▶ Fault injection

- ✓ Disturbance injection induces malfunction in the circuit operation.
  - Laser, Voltage/Clock glitch, Body biasing, **Electromagnetic**



# Electromagnetic fault injection (EMFI)

## ▶ Advantages of EMFI

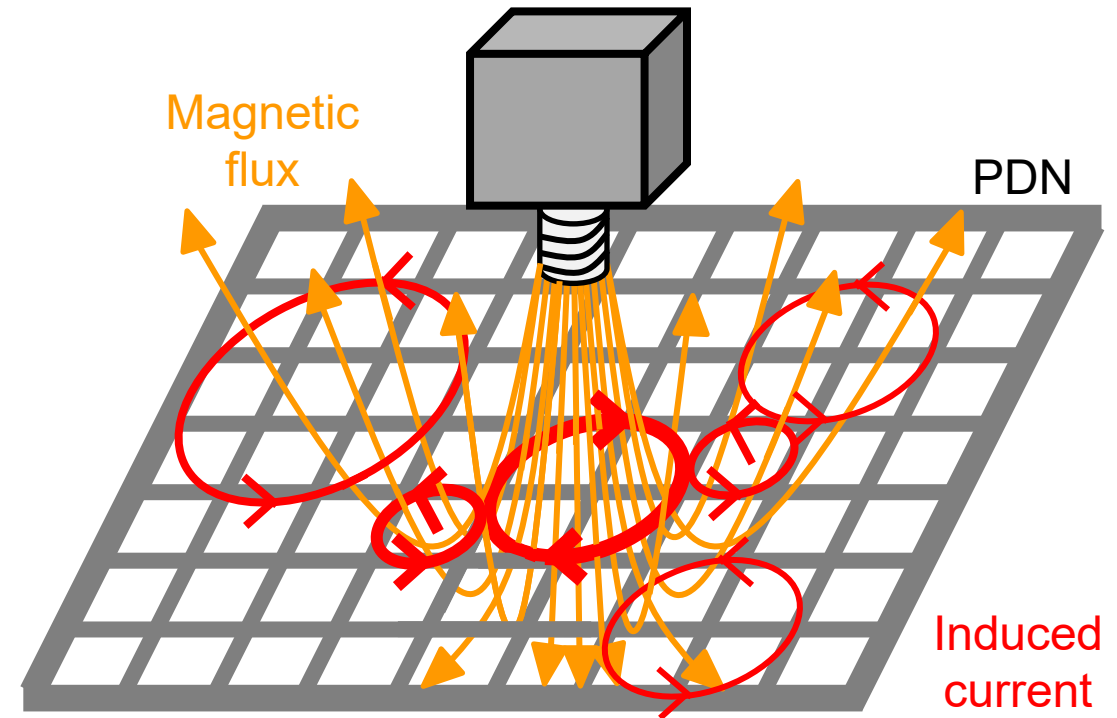
- ✓ Inexpensive and easy
- ✓ Universal to any chip assembly technology

## ▶ Attack concept

- ✓ Magnetic flux induces unwanted currents.

## ▶ Problems

- ✓ The principle is not simpler as perceived from attack concepts.
- ✓ Physical level understanding is missing.



# Outline

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1. Background
2. Deliverables
3. Measurement and evaluation
  - On-chip voltage fluctuation
  - AES digital faults
4. EM simulation
5. Conclusion

# Deliverables

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## ▶ Problems

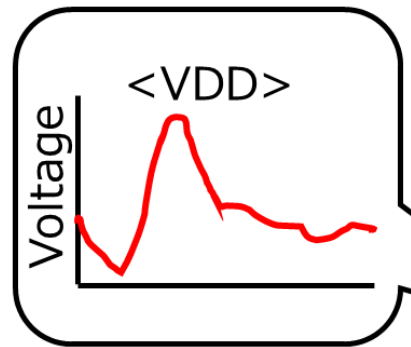
- ✓ Physical mechanisms and parameters are less involved in EMFI analyses.
- ✓ Needed more in-depth understandings from device physics

## ▶ Contributions

- ✓ EMFI voltage fluctuations visualized by on-chip measurements, correlated with digital faults
- ✓ Initial trials of EM simulation-based analysis

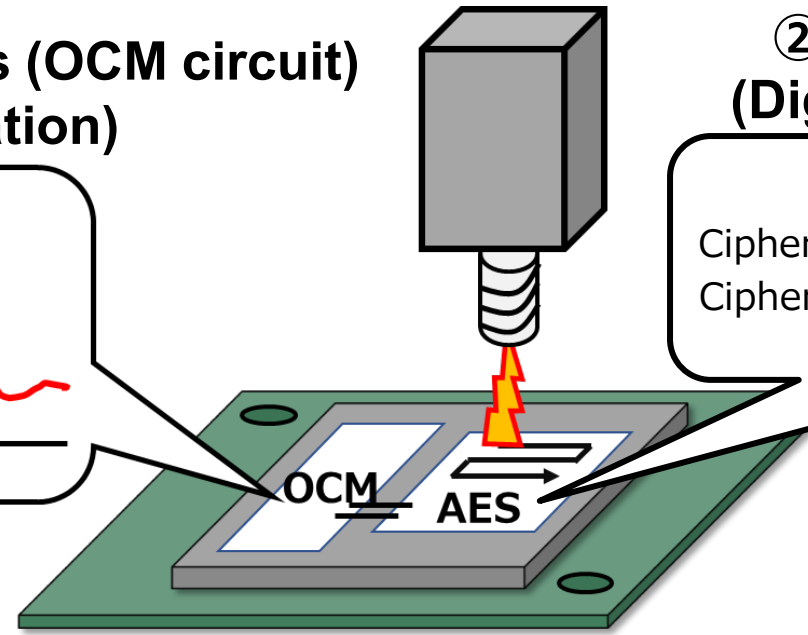
# What we did...

① On-chip measurements (OCM circuit)  
(Voltage fluctuation)

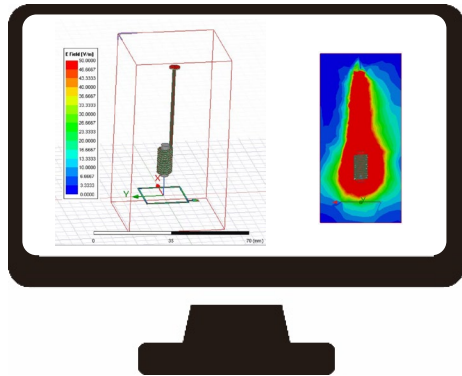


② AES fault evaluation  
(Digital fault mechanisms)

Check data	Fault
Cipher text1[0:127] X...X	⇒ ○
Cipher text2[0:127] X...X	⇒ ×
⋮	



③ EM simulation  
(Voltage fluctuation)

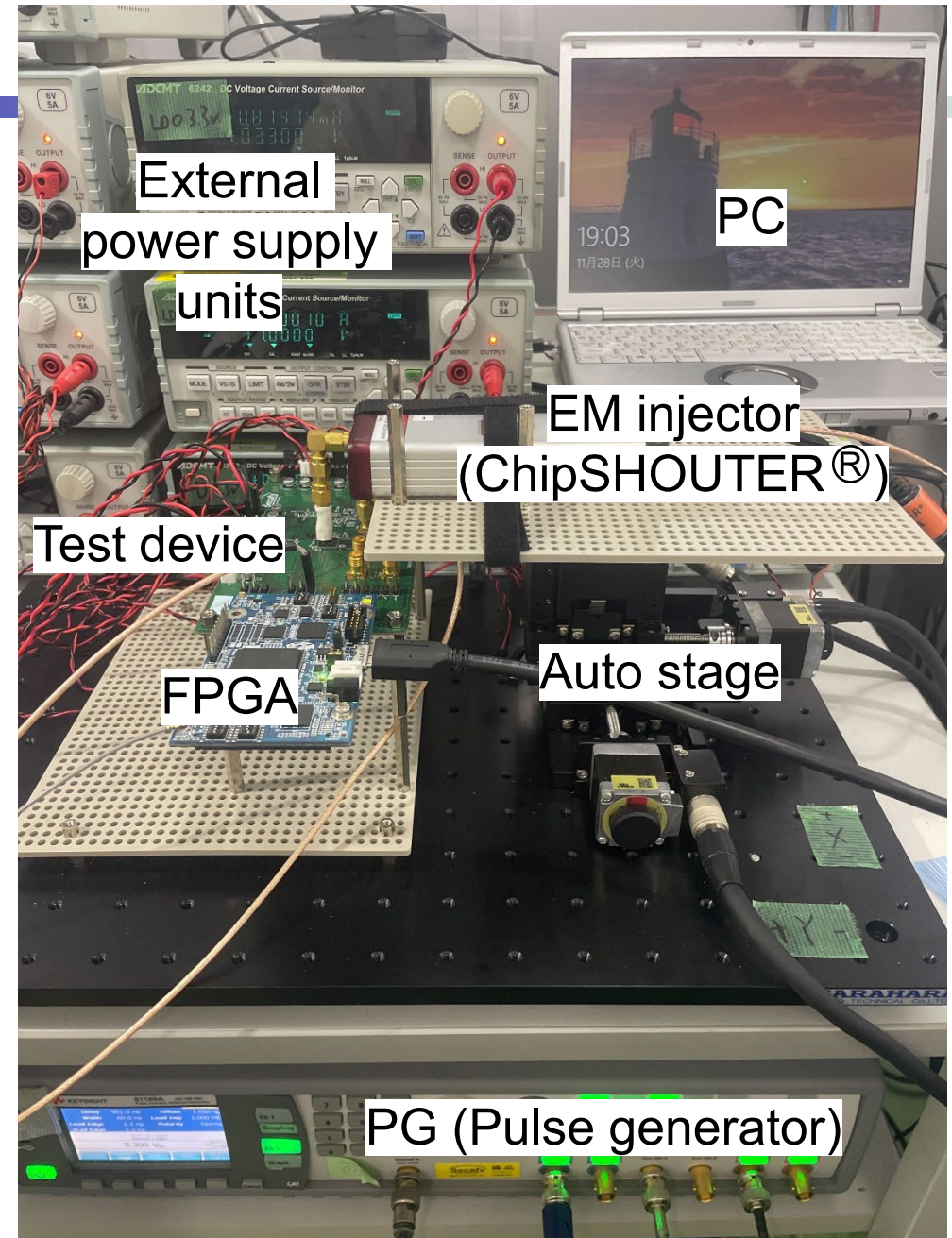
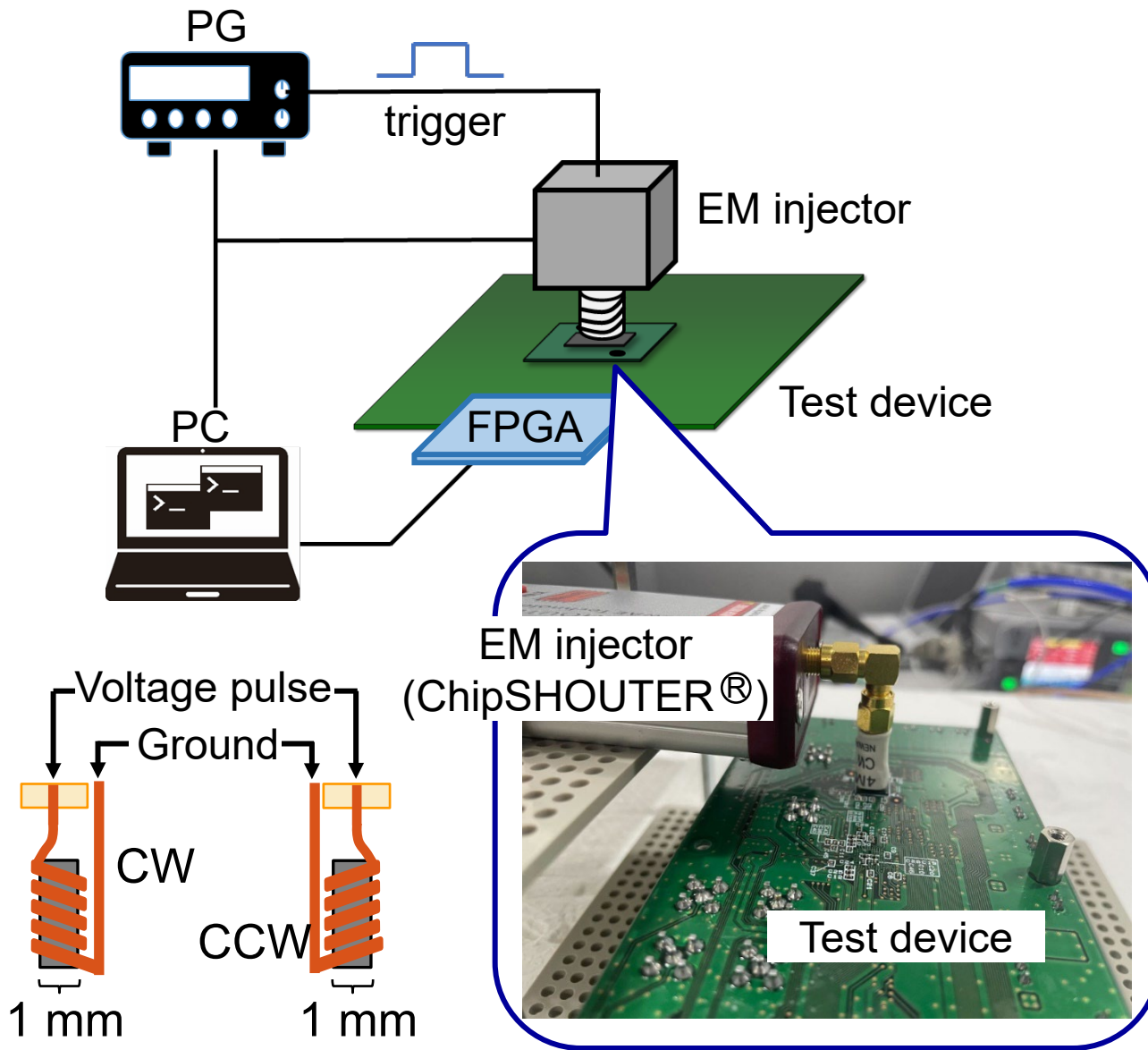


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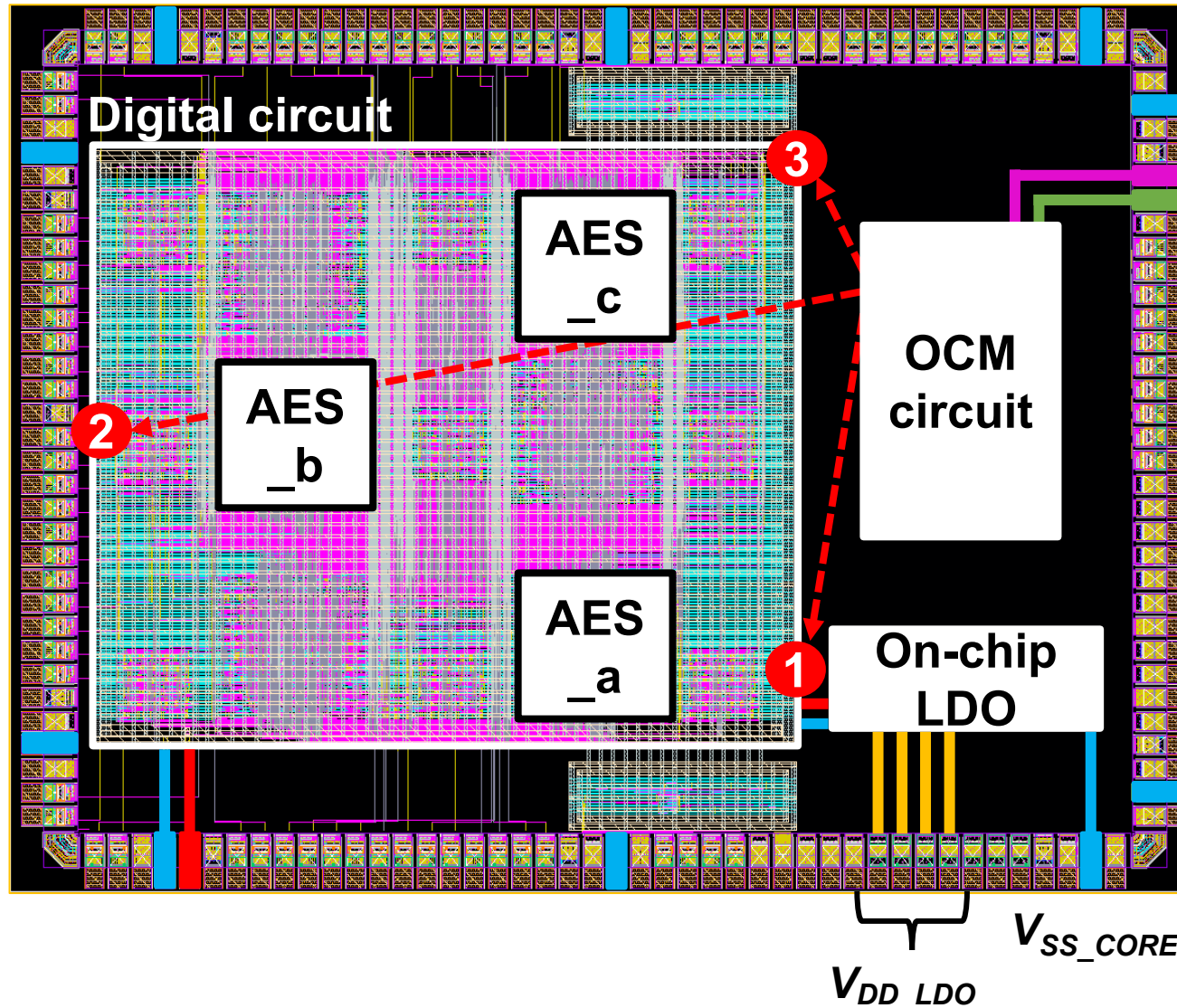
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# Evaluation setup

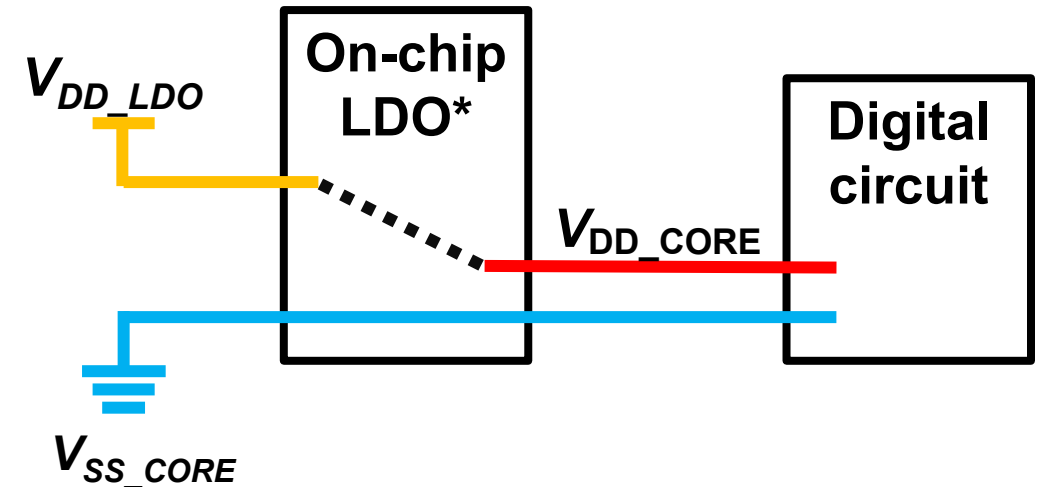




# Test chip



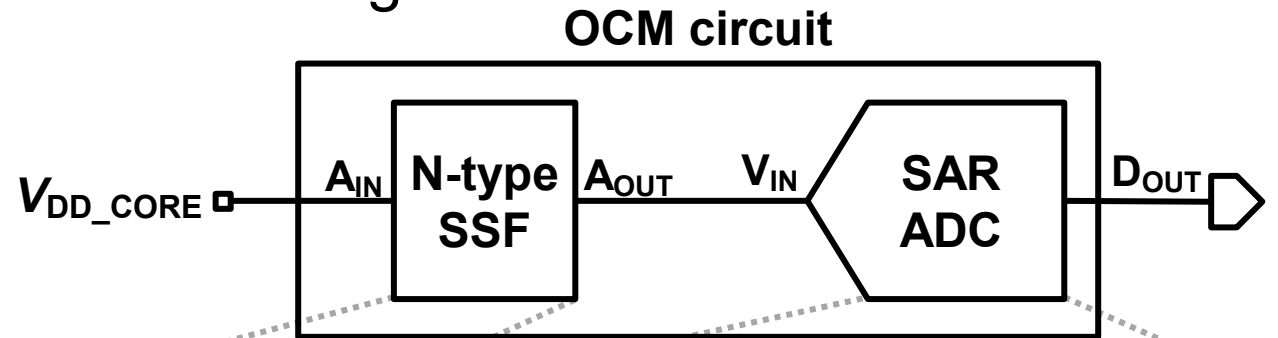
- ▶ 180 nm CMOS
- ▶ Flip-chip BGA
- ▶ Chip size : 3 mm x 4 mm



\*LDO : Low drop-out voltage regulator

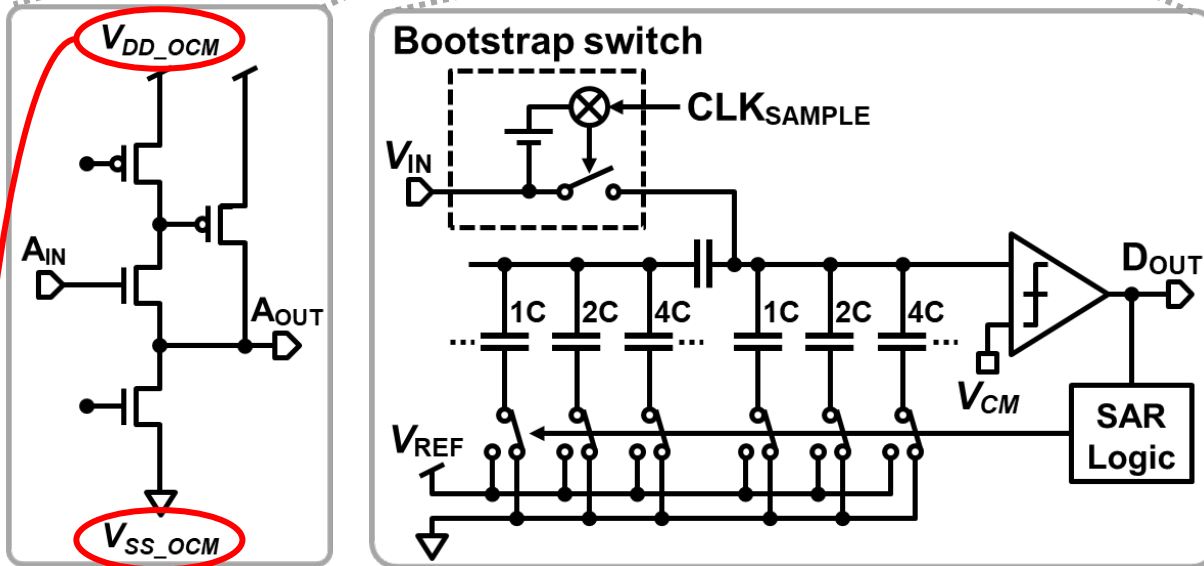
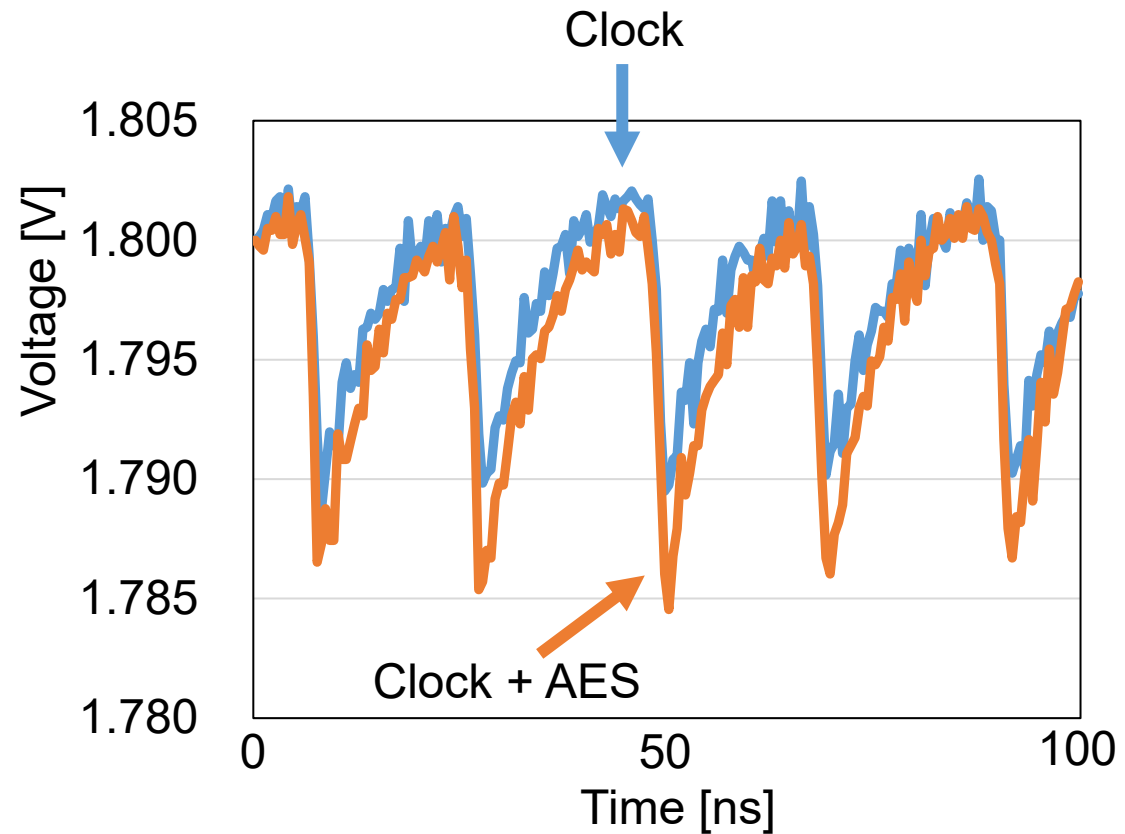
# OCM circuits and on-chip waveforms

▶ Circuit diagrams



▶ Power noise waveforms

- ✓ Differences due to the scale of the circuit in operation

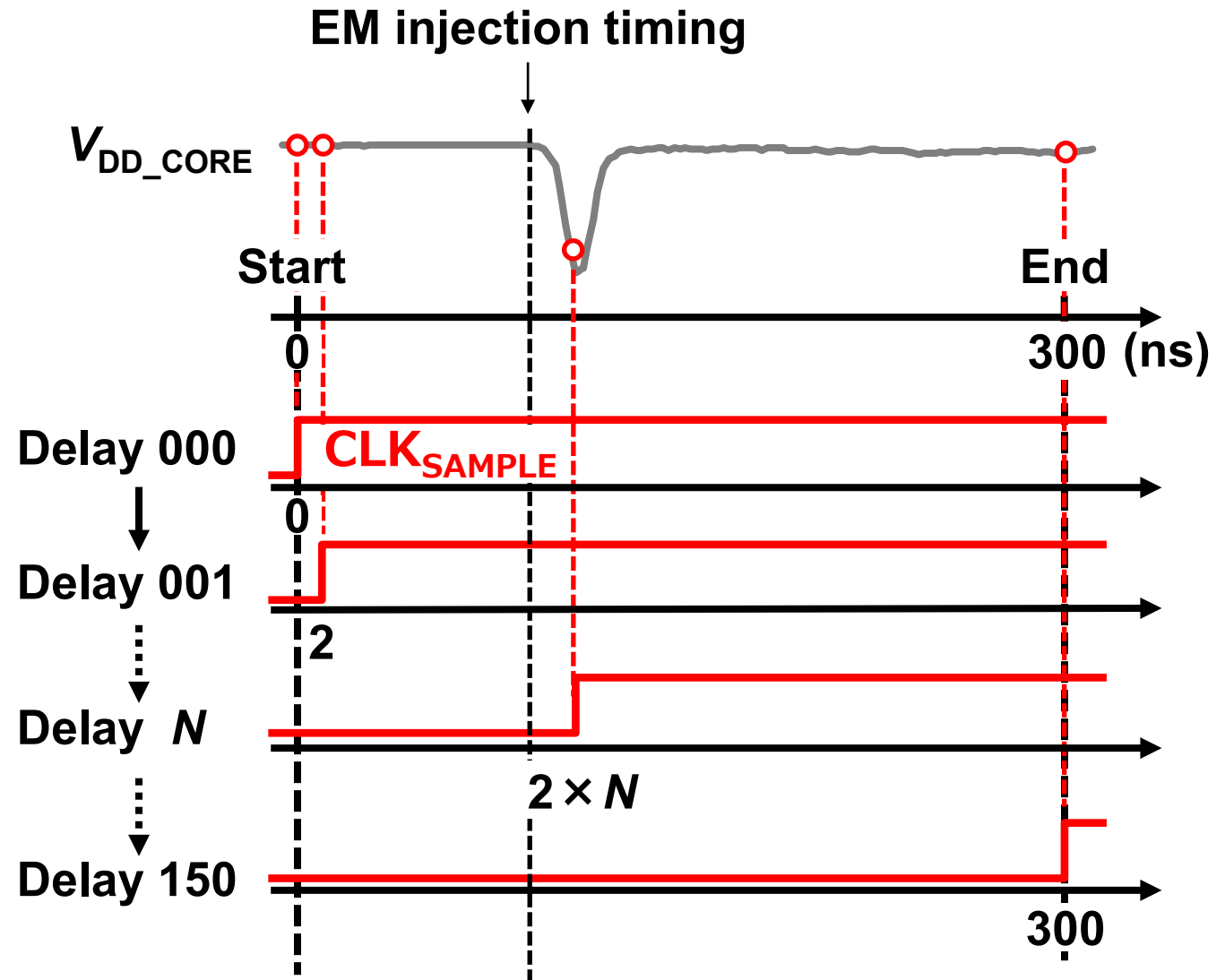
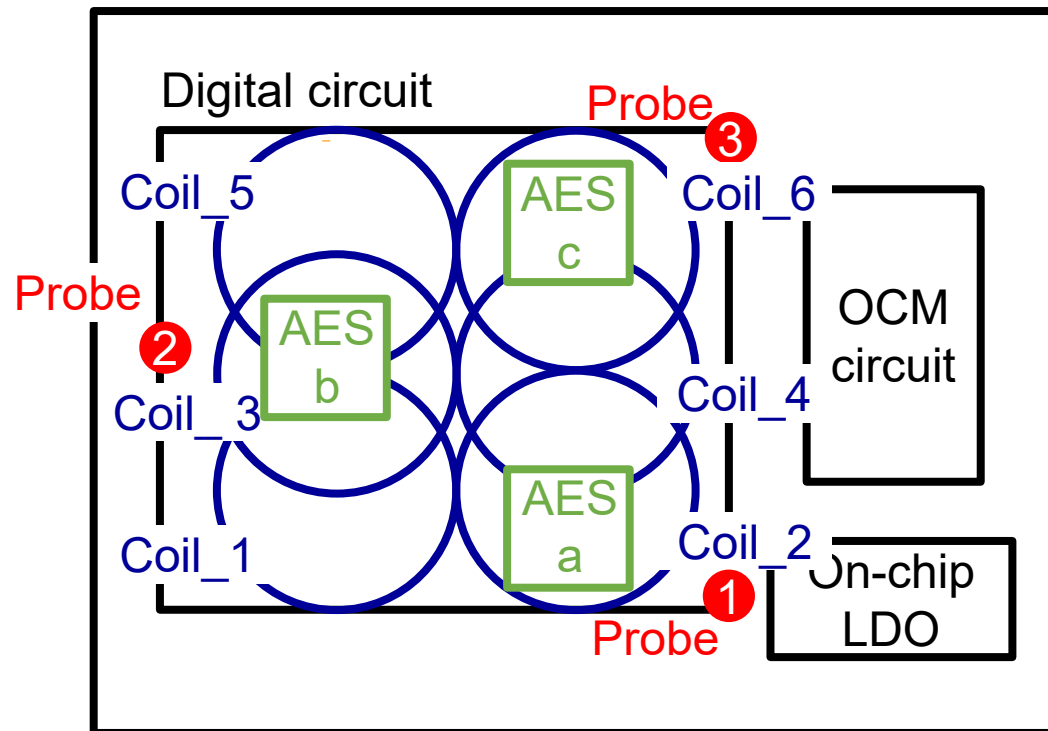


Isolated from digital circuit

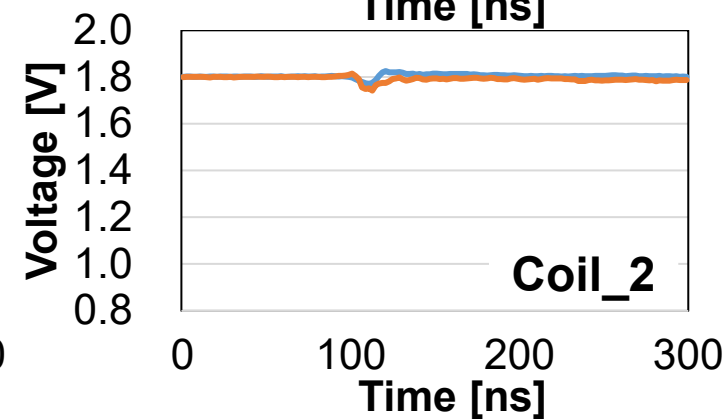
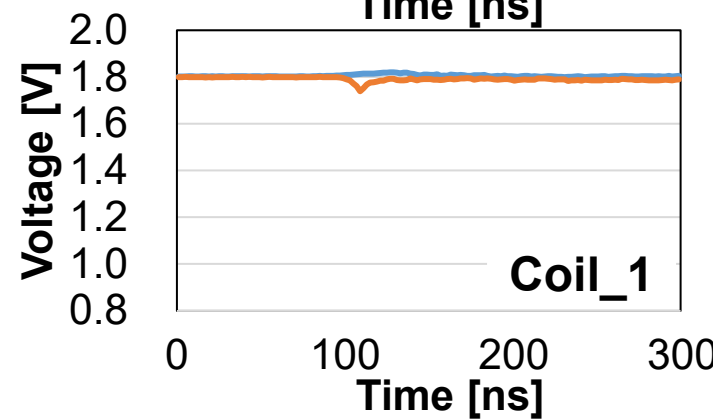
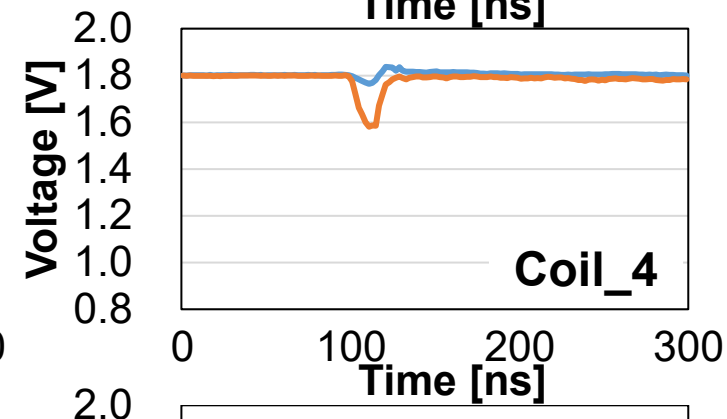
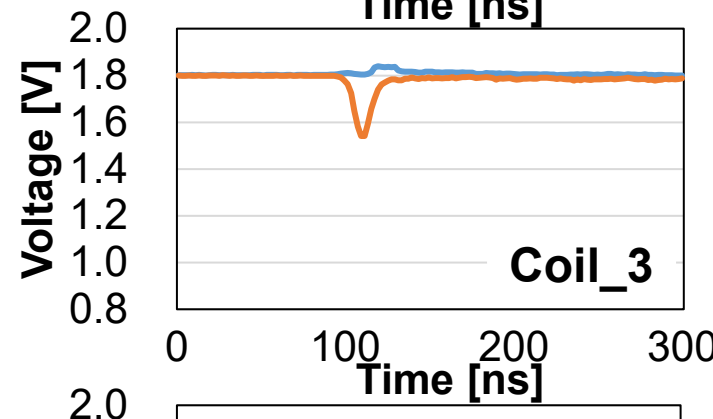
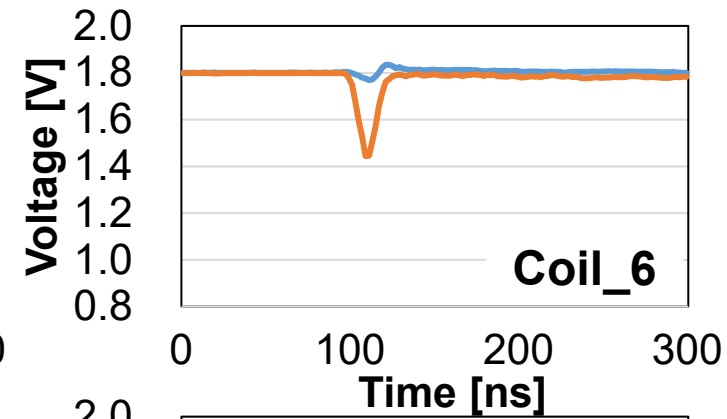
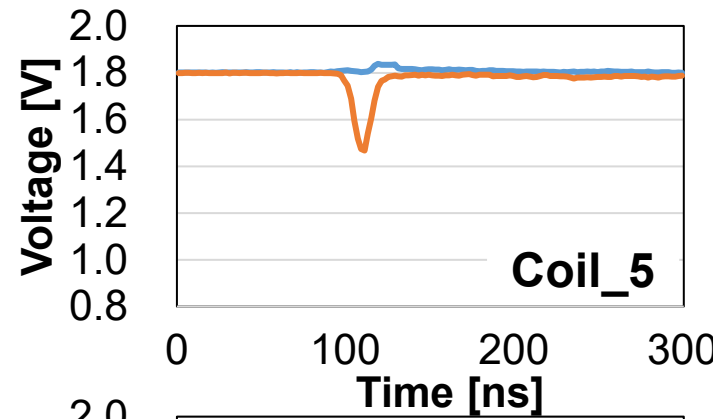
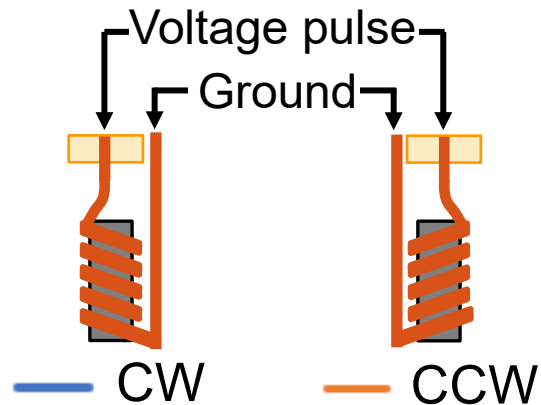
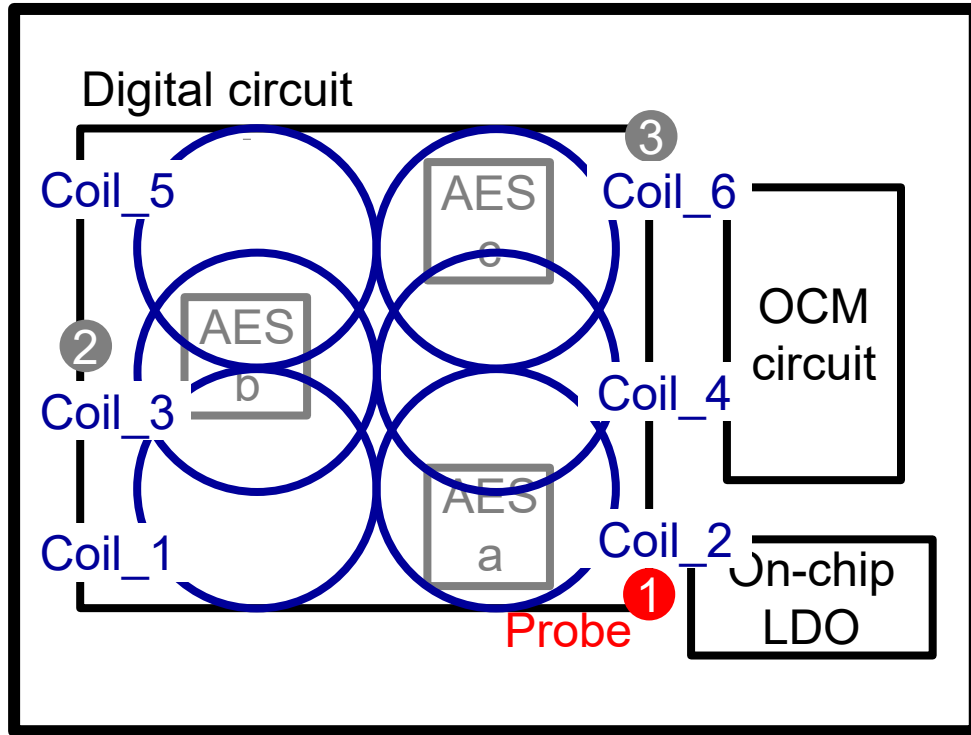
- ✓ Frequency bandwidth : 1 GHz
- ✓ Voltage resolution: 11 bit, 1 mV for 1 Vpp

# EMFI on-chip voltage measurements

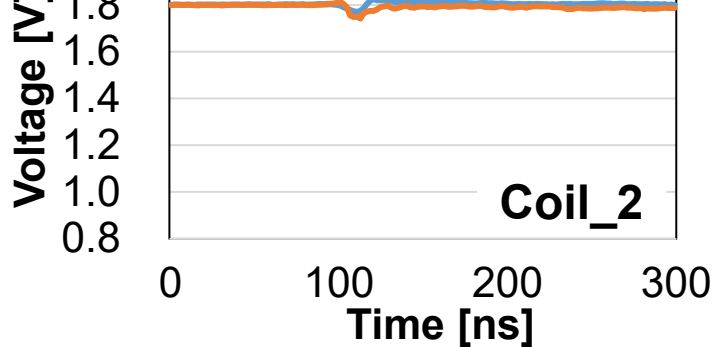
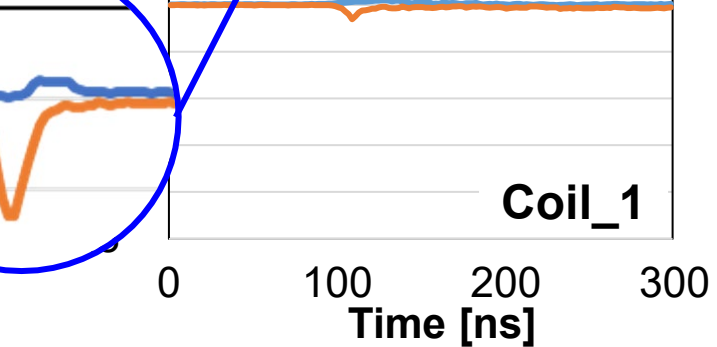
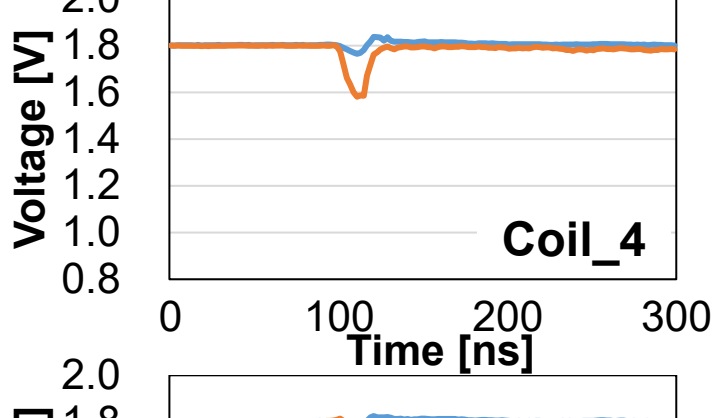
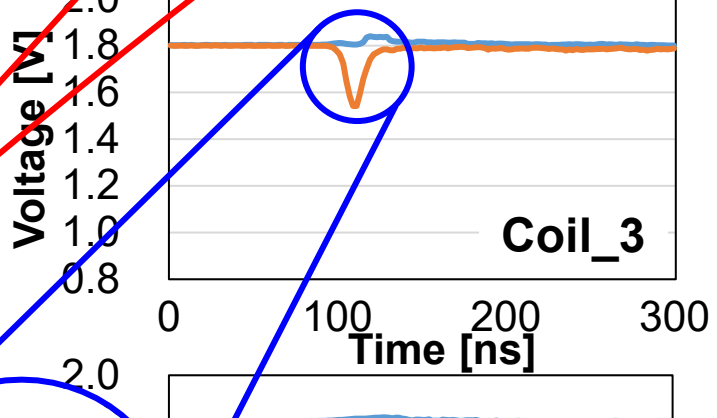
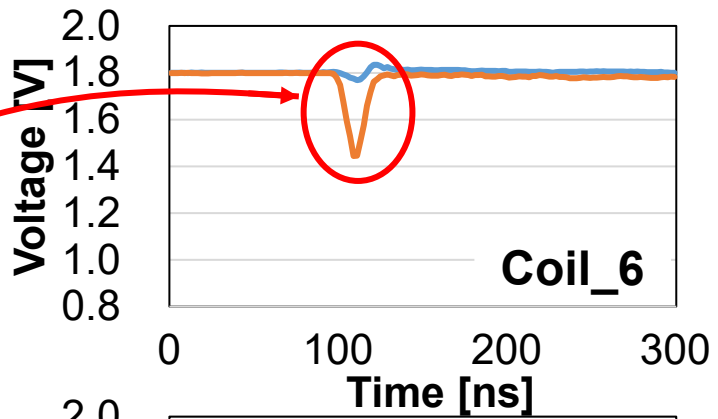
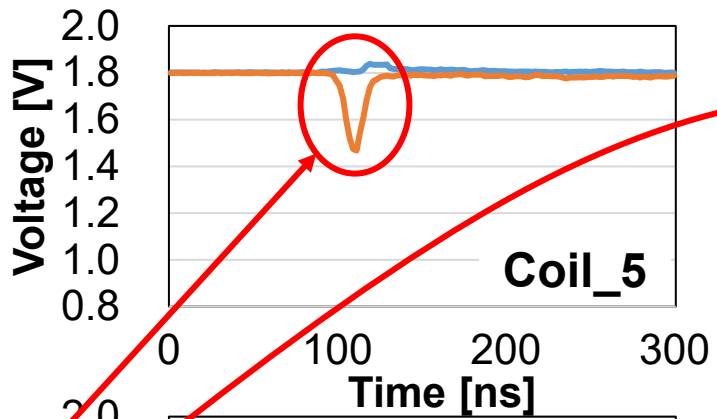
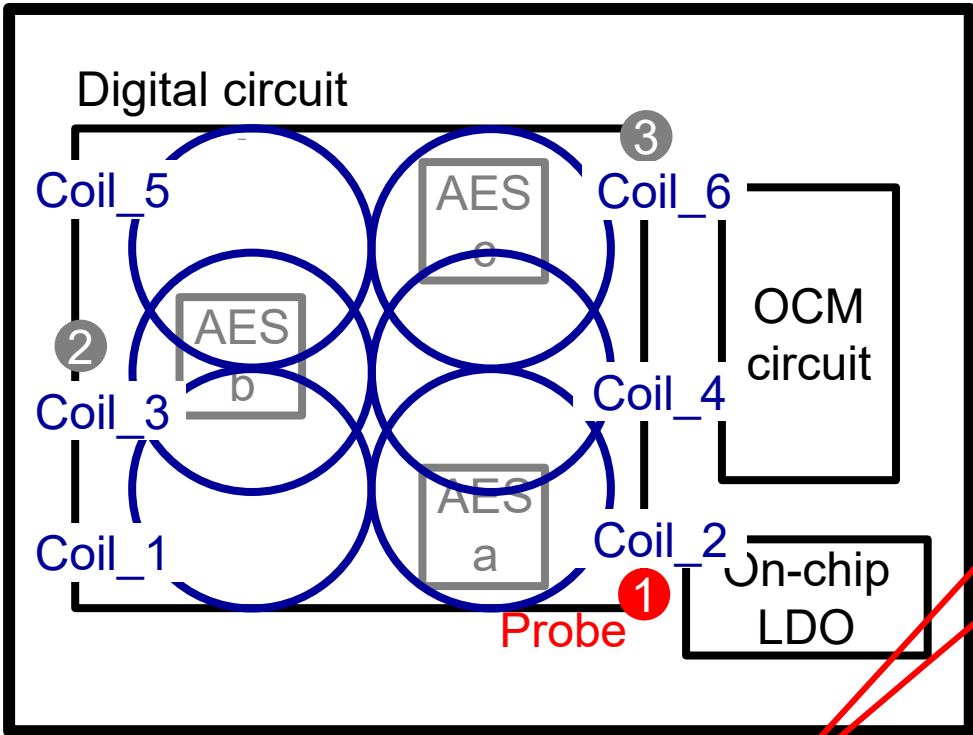
- ▶ Waveform acquisition under EMFI
- ▶ Time equivalent sampling method applied in measurement



# Measurement results

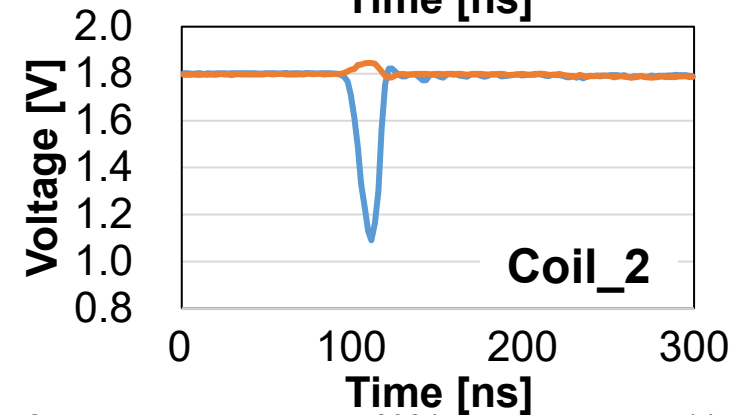
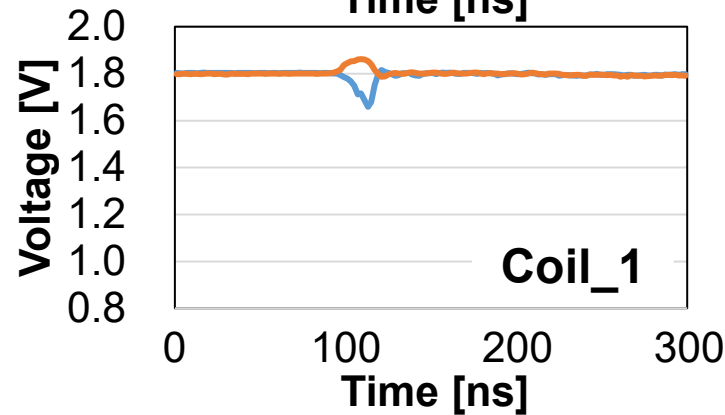
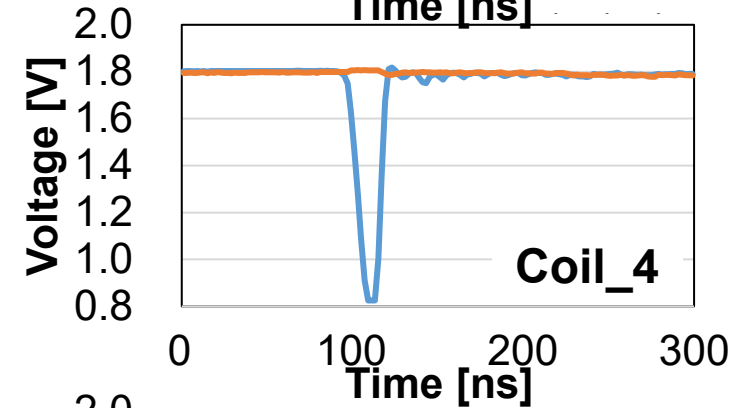
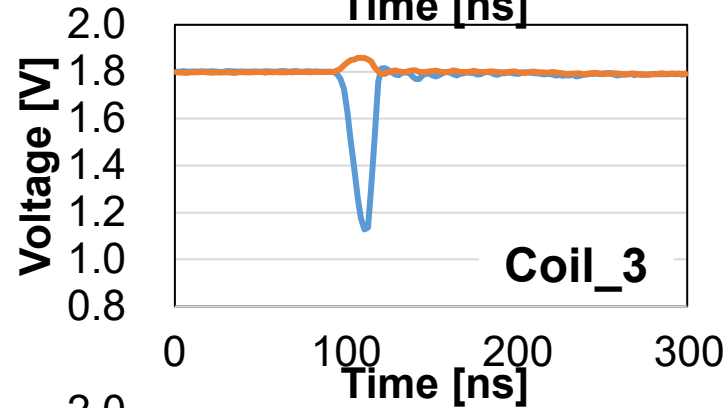
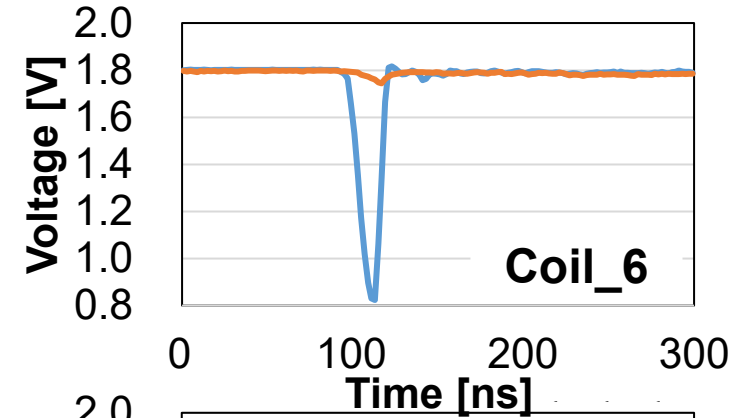
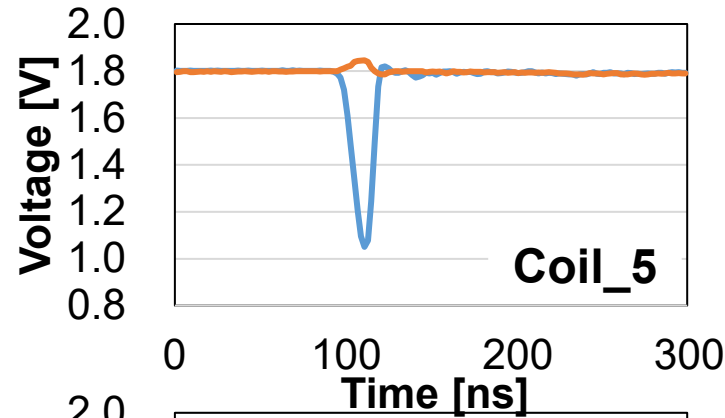
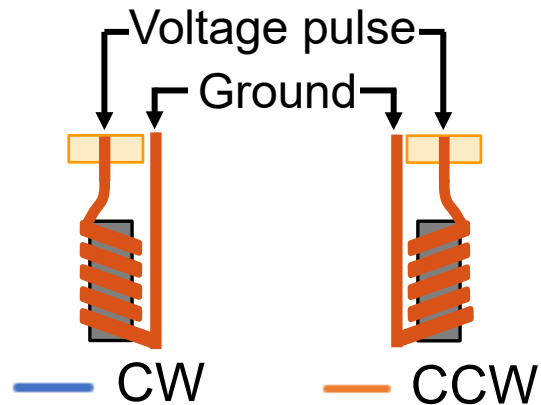
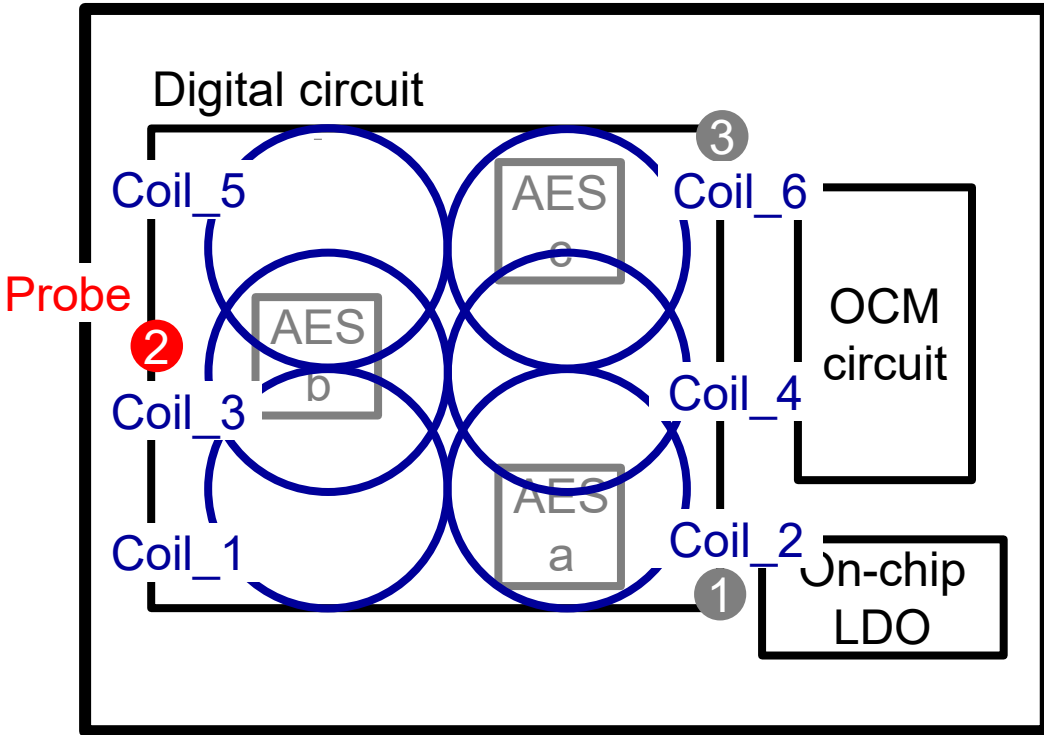


# Findings from measurements

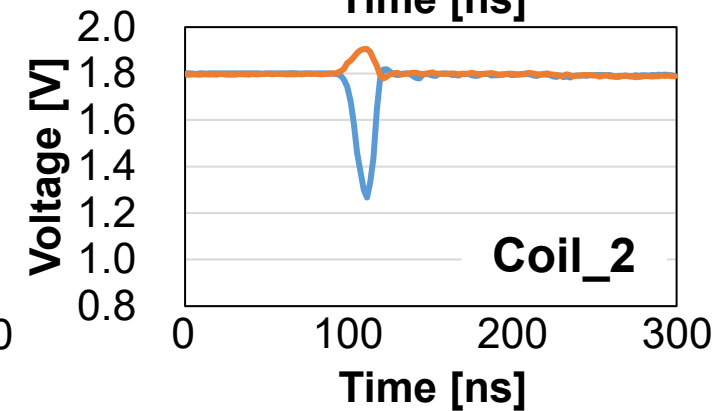
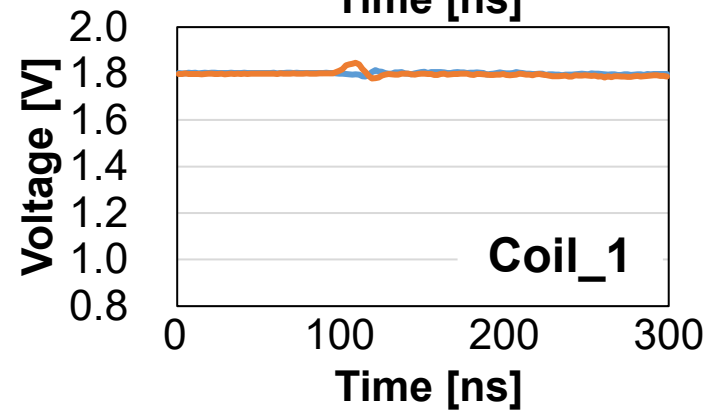
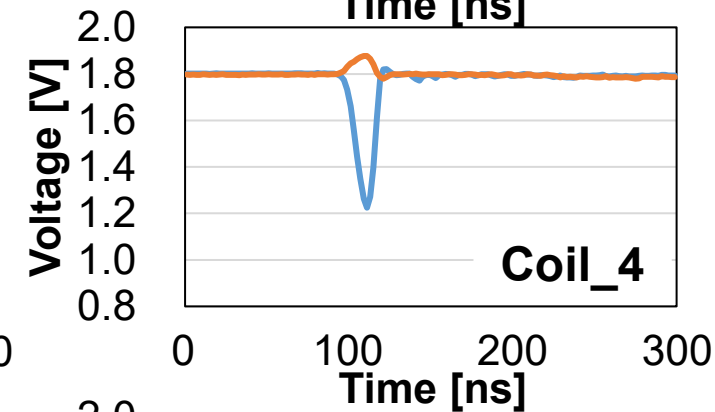
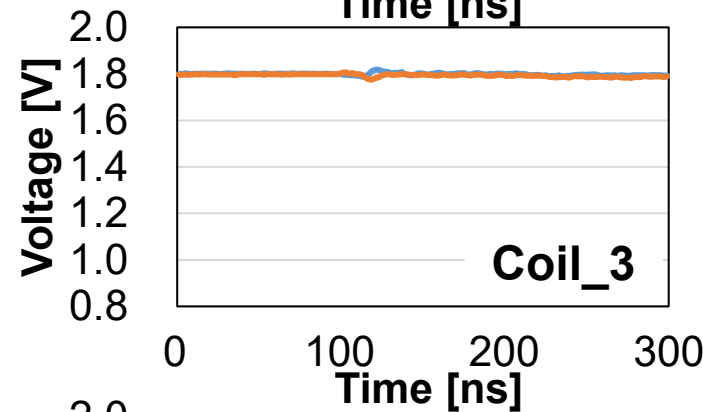
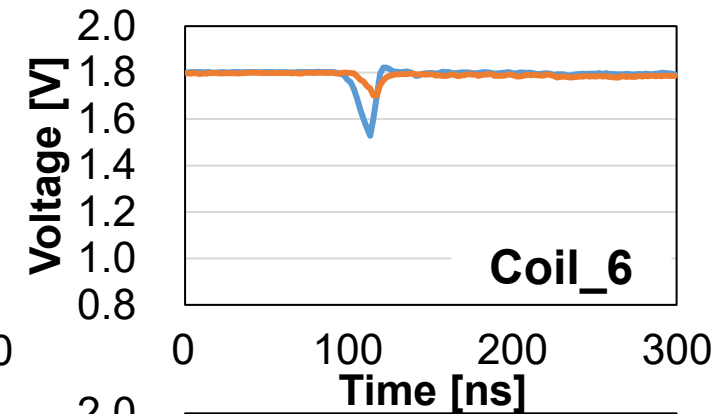
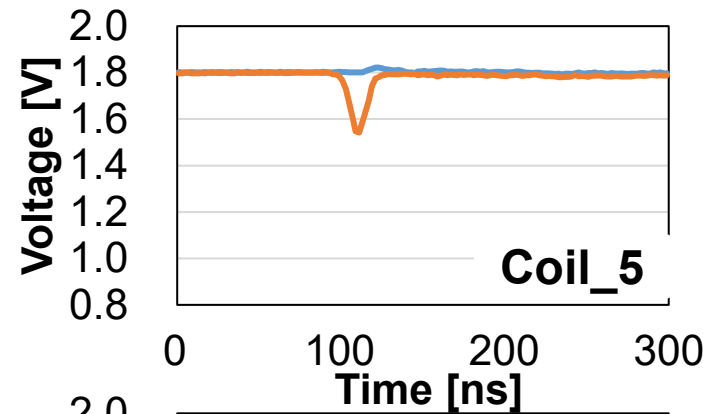
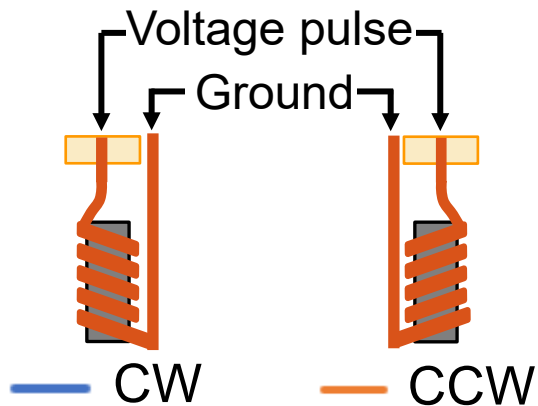
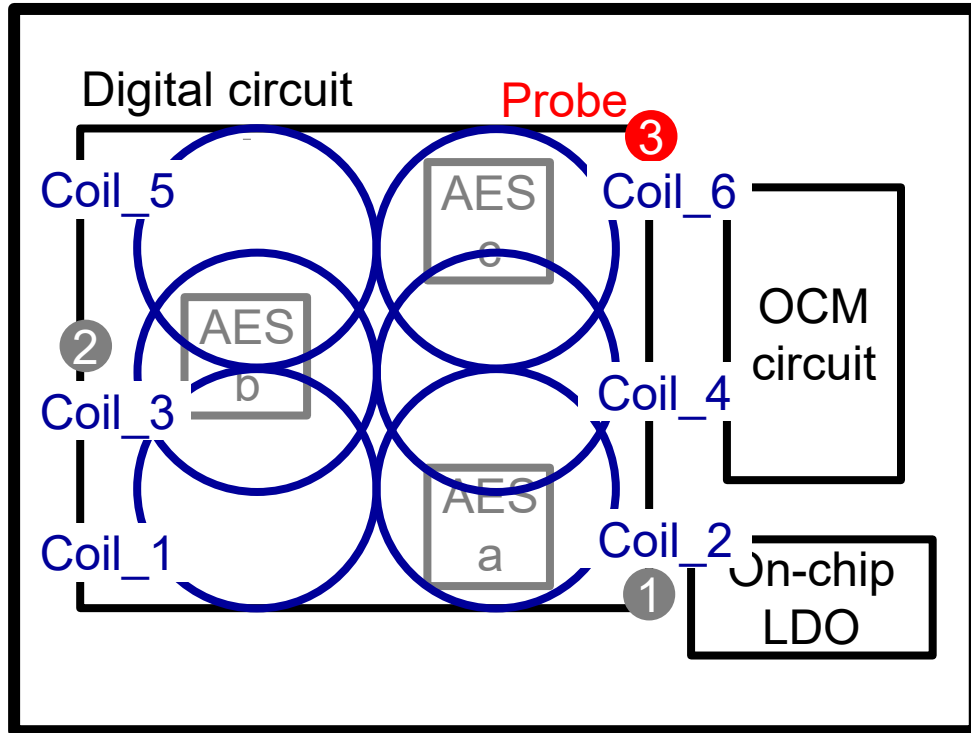


- ▶ Large drops in areas far from the coil
- ▶ Both positive and negative voltage fluctuation

# Measurement results



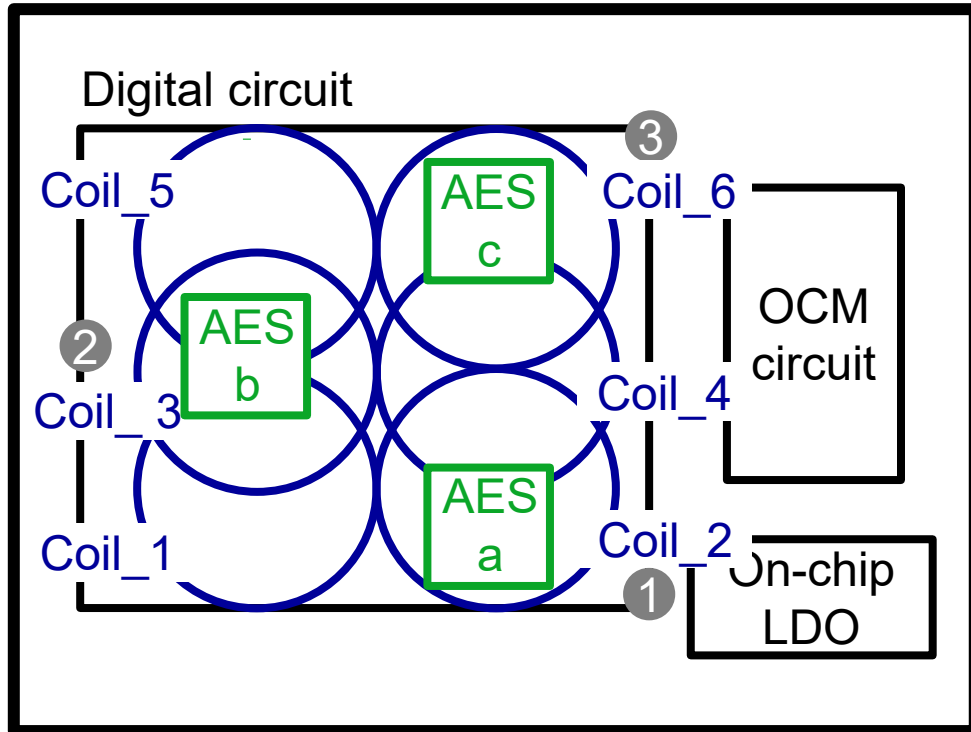
# Measurement results







# Evaluation results

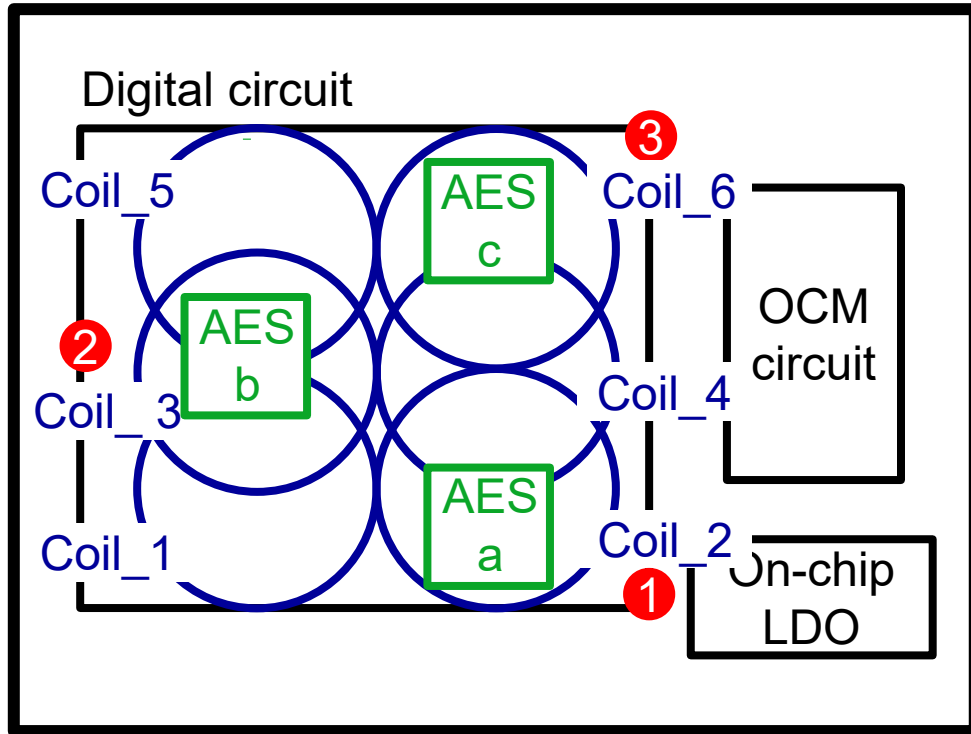


## ► Key findings

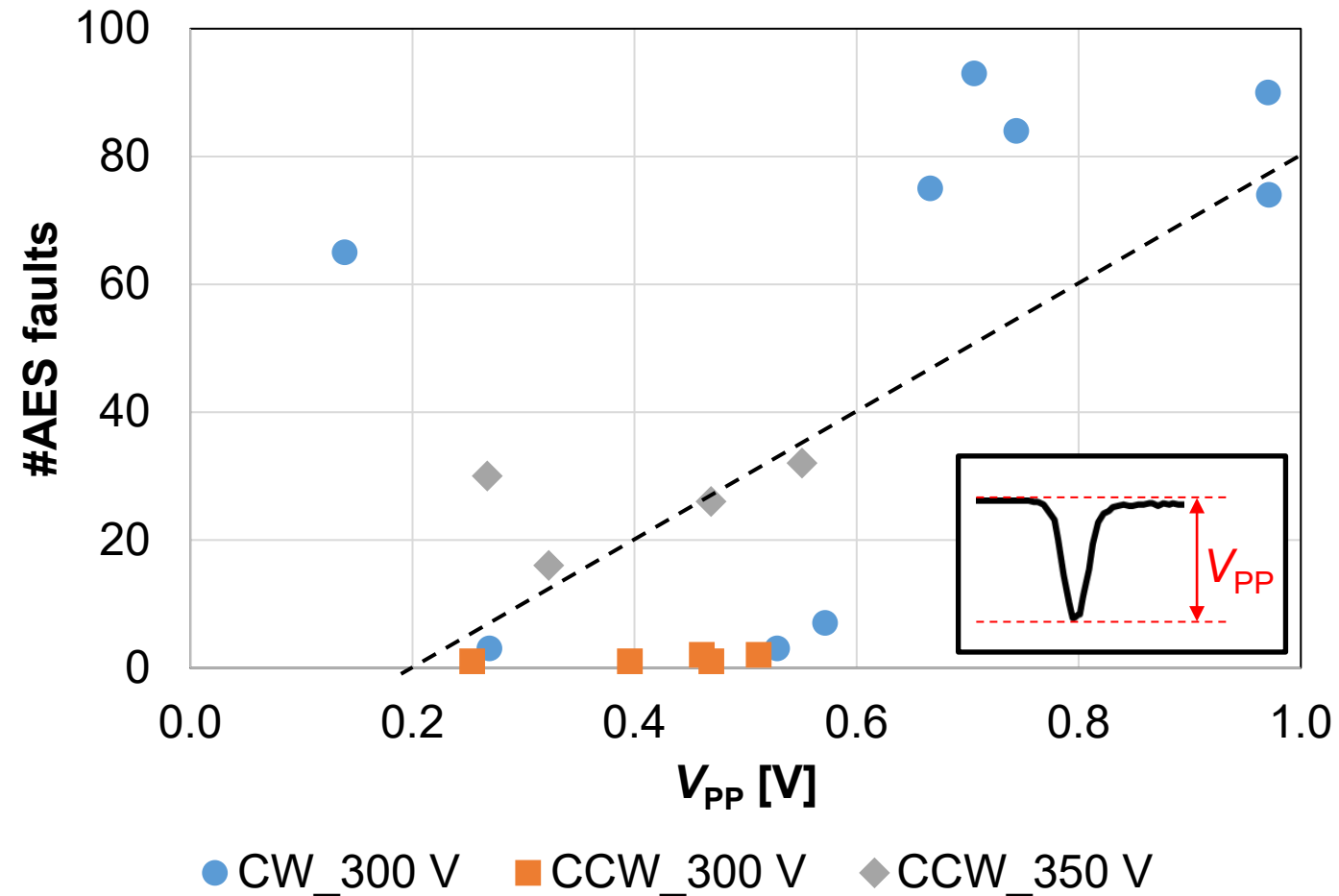
- ✓ # of digital faults reflect different layout positions among identical AES cores

CW				CCW			
AES_c				AES_c			
Coil_5	<b>6</b>	Coil_6	3	Coil_5	1	Coil_6	3
Coil_3	1	Coil_4	<b>7</b>	Coil_3	1	Coil_4	2
Coil_1	2	Coil_2	3	Coil_1	1	Coil_2	2
AES_b				AES_b			
Coil_5	<b>84</b>	Coil_6	<b>74</b>	Coil_5	1	Coil_6	1
Coil_3	<b>75</b>	Coil_4	<b>90</b>	Coil_3	1	Coil_4	0
Coil_1	<b>65</b>	Coil_2	<b>93</b>	Coil_1	1	Coil_2	1
AES_a				AES_a			
Coil_5	<b>9</b>	Coil_6	<b>6</b>	Coil_5	2	Coil_6	1
Coil_3	3	Coil_4	<b>13</b>	Coil_3	2	Coil_4	1
Coil_1	4	Coil_2	2	Coil_1	4	Coil_2	1

# Analysis : Voltage fluctuations and AES faults



► On-chip voltage fluctuations and AES digital faults are correlated



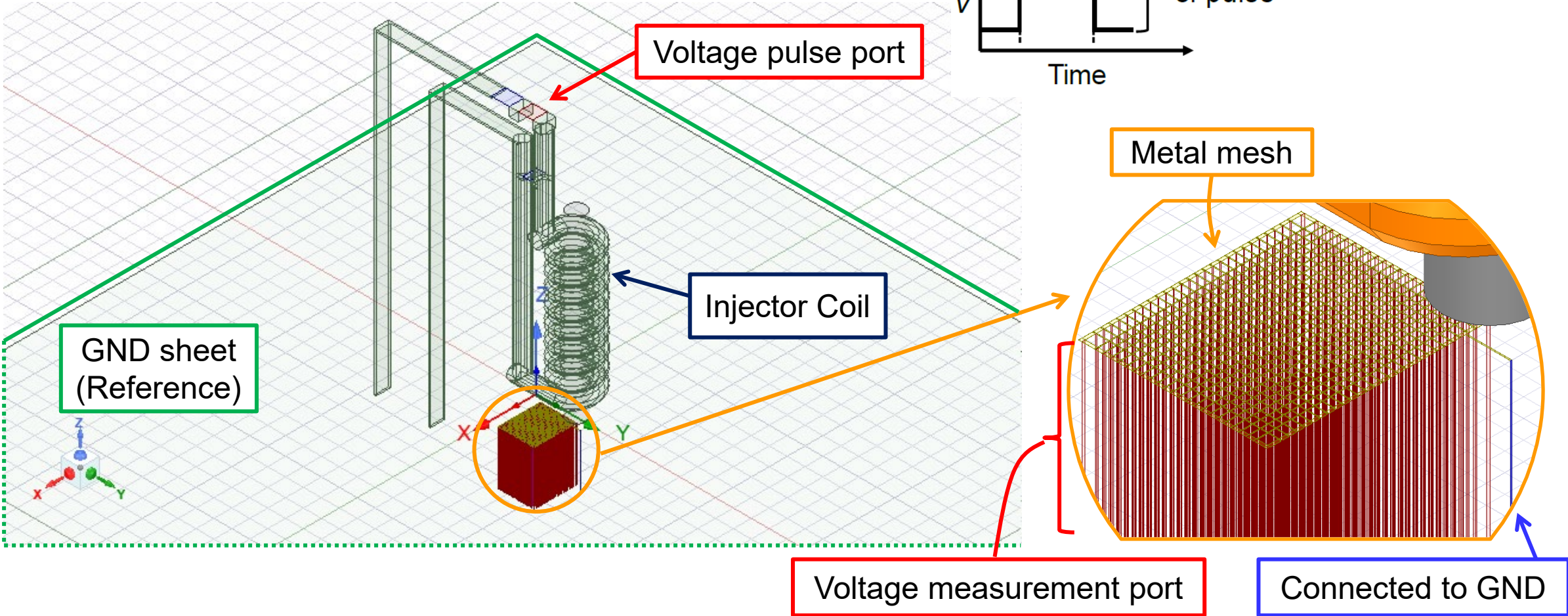
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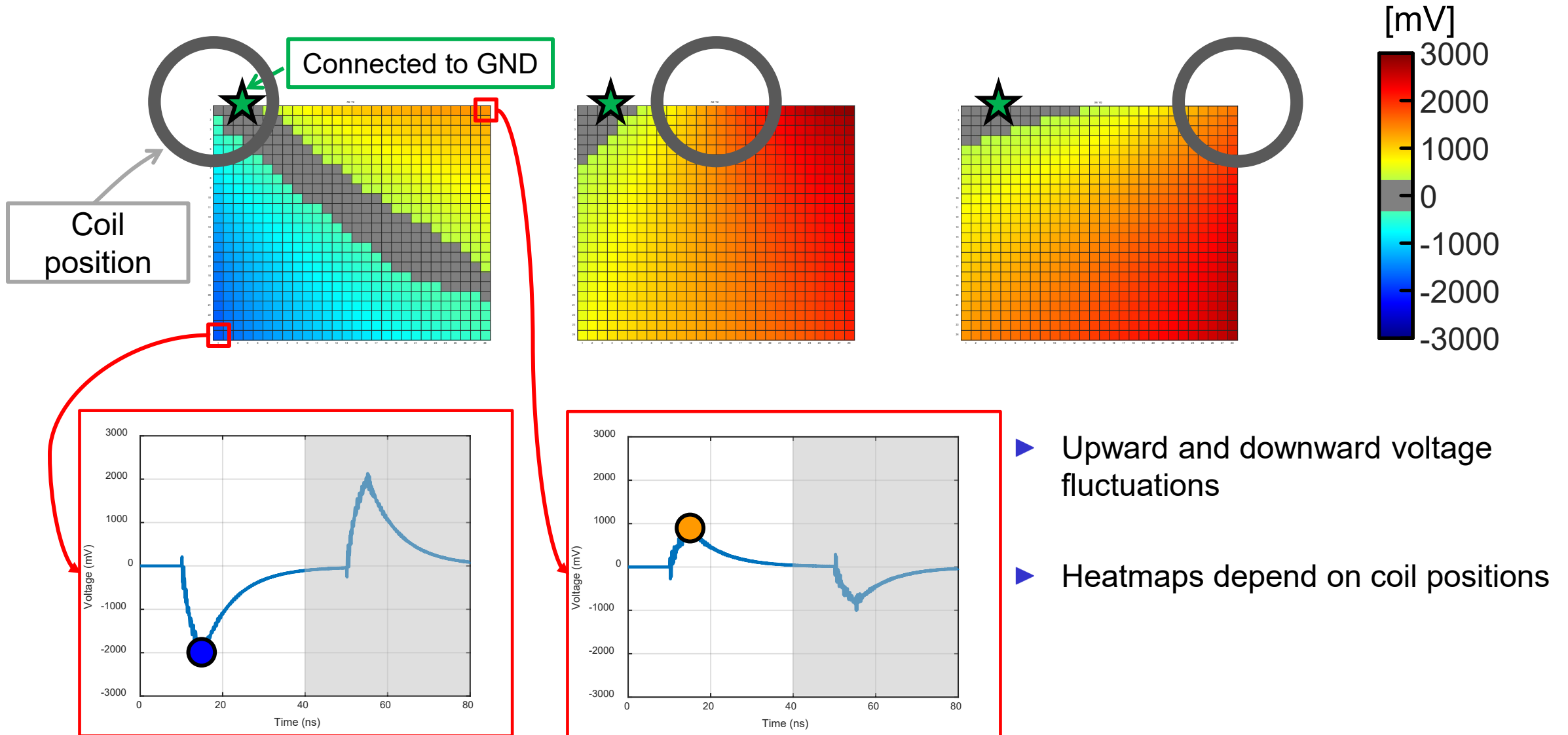
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# EM simulation trials

▶ Simulation models built for EM field solver



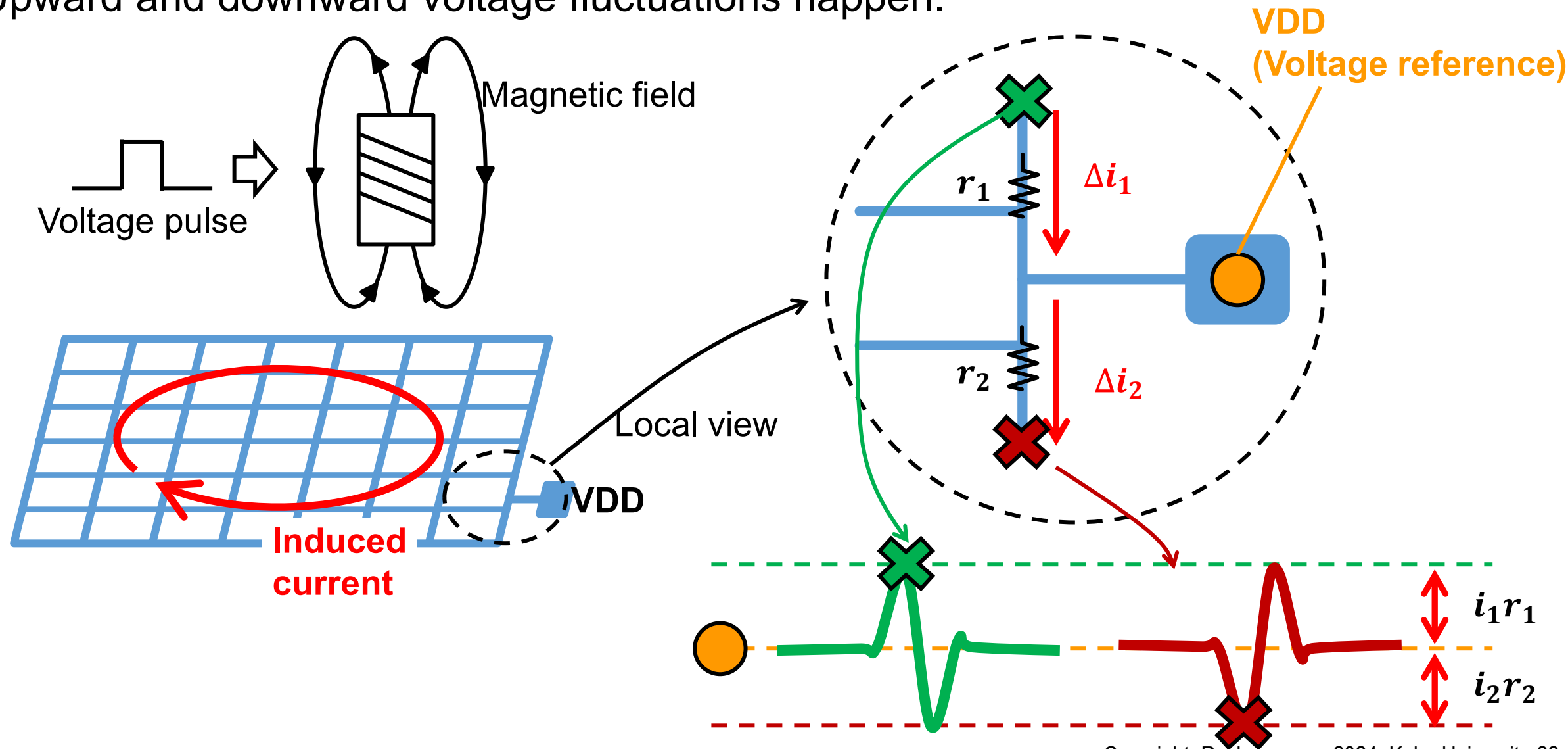
# Simulation results



- ▶ Upward and downward voltage fluctuations
- ▶ Heatmaps depend on coil positions

# Interpretation

- ▶ Upward and downward voltage fluctuations happen.



# Conclusion

- ▶ EMFI voltage fluctuations visualized by on-chip measurements
  - ✓ Large drops in areas far from the coil
  - ✓ Both positive and negative voltage fluctuation
  
- ▶ Digital fault evaluation
  - ✓ On-chip voltage fluctuations and AES digital faults are correlated
  
- ▶ EM simulation trial
  - ✓ Positive and negative voltage fluctuations happen.

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and by SECOM Science and Technology Foundation